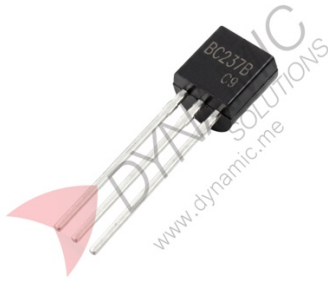


BC237B NPN General Purpose Transistor



Features:

The BC237B NPN Transistor is a low current, low voltage silicon transistor in a TO-92 package. It is designed for general purpose switching and amplification applications and supports 45V collector-emitter voltage, 100 mA collector current, 350 mW power dissipation, and 150 MHz transition frequency.

Specifications	
Part Number	BC237B
Device Type	NPN silicon transistor
Case	TO-92
Polarity	NPN
Collector-Base Voltage	50V
Collector-Emitter Voltage	45V
Emitter-Base Voltage	6V
Collector Current DC	100 mA
Peak Collector Current	200 mA
Peak Base Current	200 mA
Collector Power Dissipation	350 mW
Derating Above 25°C	3.0 mW/°C
DC Current Gain hFE	200 min, 460 max
Collector Cutoff Current	15 nA max
Emitter Cutoff Current	100 nA max
Collector-Emitter Saturation Voltage	600 mV max
Base-Emitter Saturation Voltage	1200 mV max
Base-Emitter Voltage	580 mV min, 700 mV max
Collector Capacitance	5 pF
Emitter Capacitance	1.5 pF
Transition Frequency	150 MHz
Noise Figure	10 dB max
Operating Ambient Temperature	-65°C to 150°C
Storage Temperature Range	-65°C to 150°C
Junction Temperature	150°C
Mounting Type	Through hole
Surface Mounted	No
Dimensions	1.9x0.4x0.3xm

Applications	General purpose switching and amplification
Usage	Low current switching, small signal amplification, and general electronic circuits

Pinouts:

Pin Name	Description
C	Collector terminal where current enters the transistor
B	Base terminal controls transistor switching or amplification
E	Emitter terminal where current exits the transistor

Product Pictures:

